

# *Timing performance of small cell 3D silicon detectors*

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# Motivation

LGADs are the choice for timing detectors at HL-LHC and possibly 4D tracking in the future, but:

- ▶ radiation hardness is a problem – gain loss with fluence
- ▶ fill factor is a problem, especially when the cell size decreases
  - $1.3 \times 1.3 \text{ mm}^2$  – 86% with  $100 \text{ }\mu\text{m}$  gap between the pads
  - $0.5 \times 0.5 \text{ mm}^2$  – 69% with  $100 \text{ }\mu\text{m}$  gap between the pads

How about 3D (of all types) as timing detectors?

- ▶ They have fill factor 100%
- ▶ The radiation tolerance of small cell size devices is large (in signal) and allows operation at higher bias voltages (see 32<sup>nd</sup> RD50 talks of M. Manna and A. G. Alonso)

Well ..., this is not the end of the story:

- ▶ 3D can be fast – 😊 short drift distance, but 😞 saddle regions in the field
- ▶ There is no multiplication 😞, but they can be thicker as Landau fluctuations don't matter much, so the signal can be partially compensated 😊
- ▶ The weighting field – hit position – will impact the signal 😞
- ▶ for small size sensors and large thickness the capacitance will be much larger, hence noise and the jitter
- ▶ Lower operation voltages than for LGADs and possibly lower current ( $I_{\text{LGAD}} = G \cdot I_{\text{gen}}$ ) result in smaller power dissipation

We want to evaluate all these ...



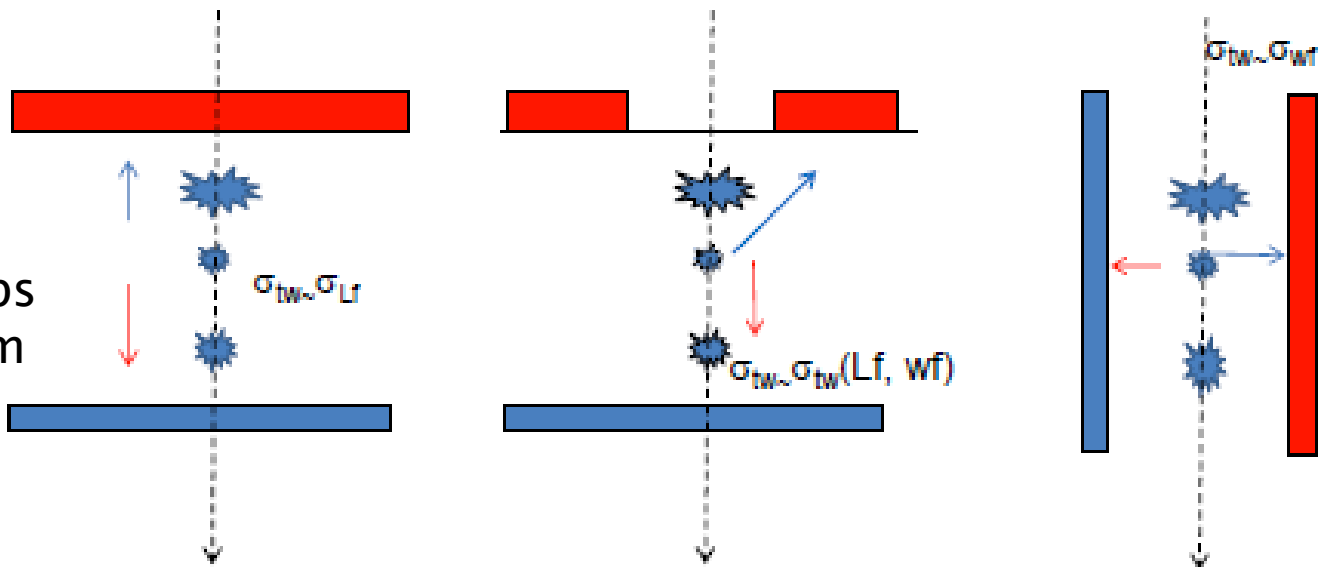
# Time resolution

$$\sigma_t^2 = \sigma_j^2 + \sigma_{tw}^2 + \sigma_{TDC}^2$$

$$\sigma_j = N/(dV/dt) \sim t_p/(S/N) \quad , \quad \sigma_{TDC} = TDC_{bin}/\sqrt{12}$$

- ▶  $\sigma_{tw}$  - **time walk component includes** (correlated - can not be summed in squares):
  - weighting field/electric field contribution -> depends on hit position in segmented devices (sometimes called distortion component)
  - Landau fluctuations in shape of the signal -> depends on hit position (segmented devices) and gain layer in LGADs
  - Landau fluctuations in amount of deposited charge -> correctable with ToA-ToT or CFD
- ▶  $\sigma_j$  - **jitter - fast rise time and high signal/noise**

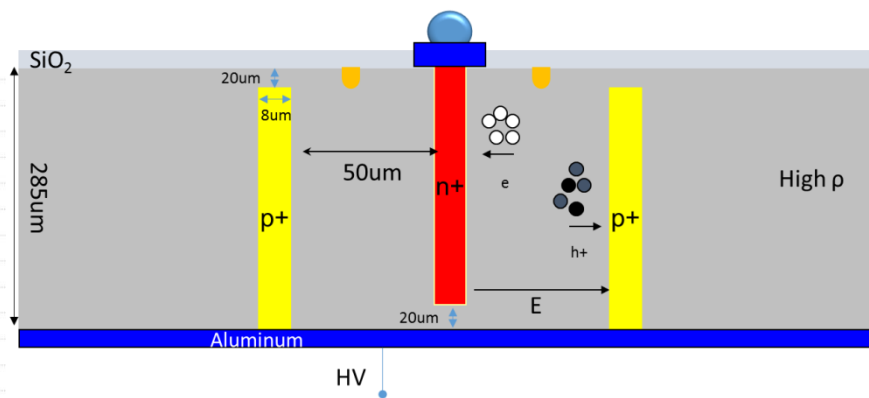
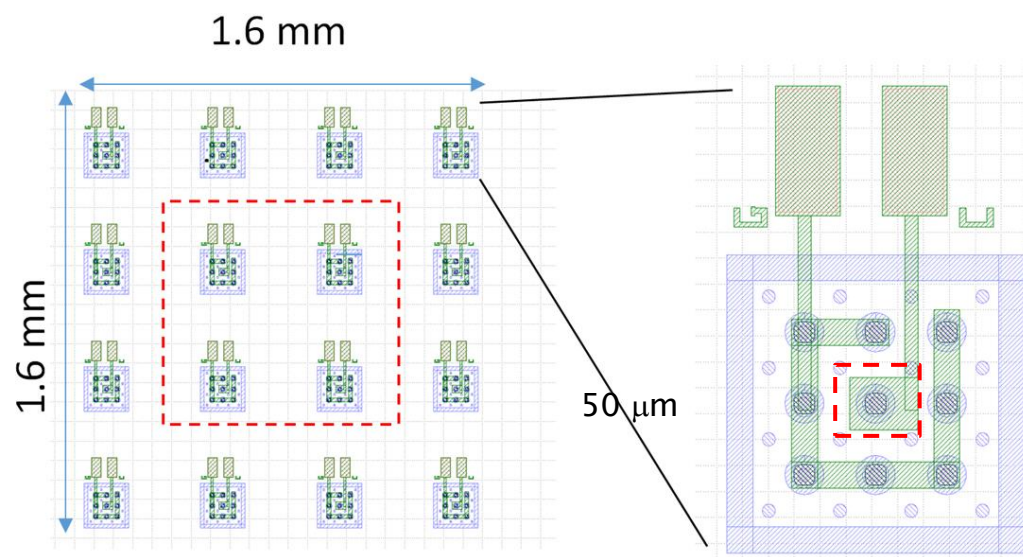
at high gain  
 $\sigma_{tw} \sim 25$  ps  
 for  $50 \mu\text{m}$   
 LGAD





# Devices under study

- ▶ CNM produced the devices almost ideal for such study – a 3x3 matrix with investigated cell in the middle and neighboring cells connected together
- ▶ cell size  $50 \times 50 \mu\text{m}^2$  – RD53 chip design
- ▶ p-type bulk ( $N_{\text{eff}} = -1.4 \cdot 10^{12} \text{ cm}^{-3}$ ), n-type collection
- ▶ 1E, holes  $2R = 8 - 10 \mu\text{m}$  and  $300 \mu\text{m}$  thick
- ▶ max operational voltage before irradiation  $\sim 50 \text{ V}$



**Such device was measured and simulated**  
(also Edge-TCT, Top-TCT scans were done, but won't be shown)

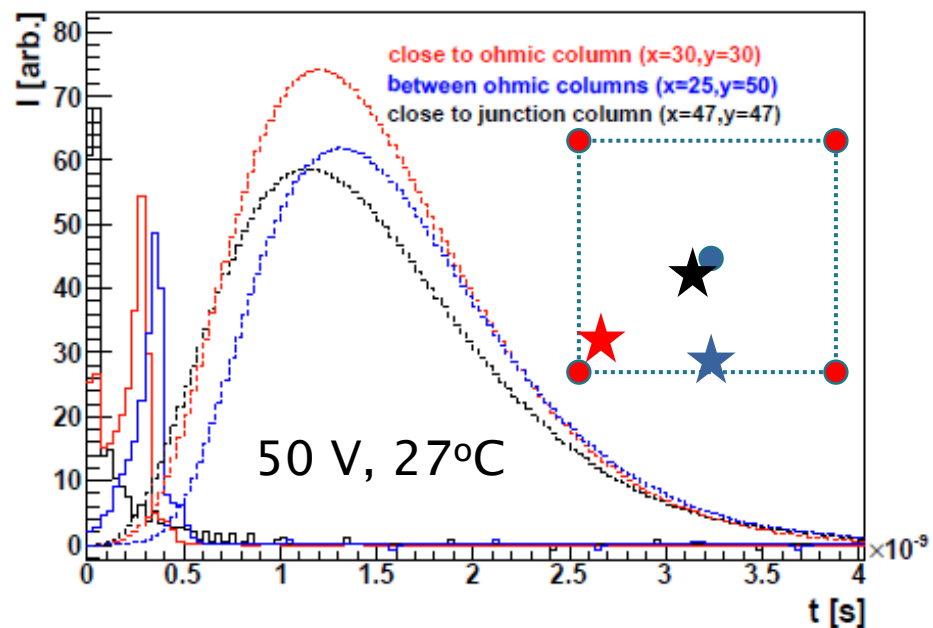
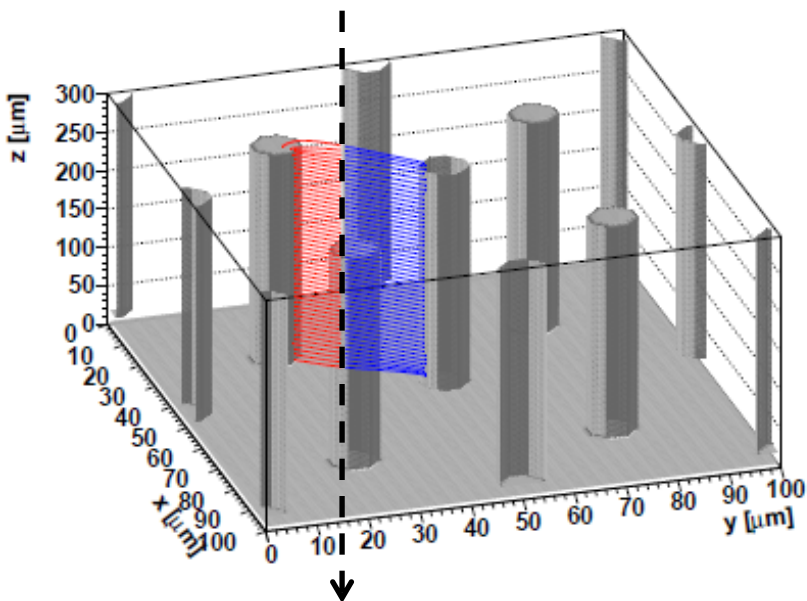


# *SIMULATION*

# Simulation of detectors



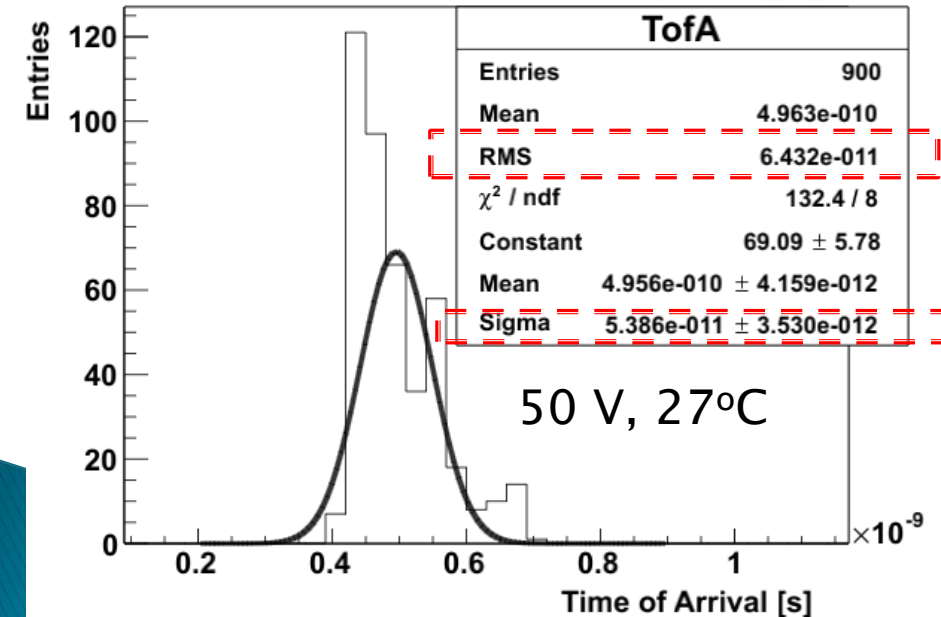
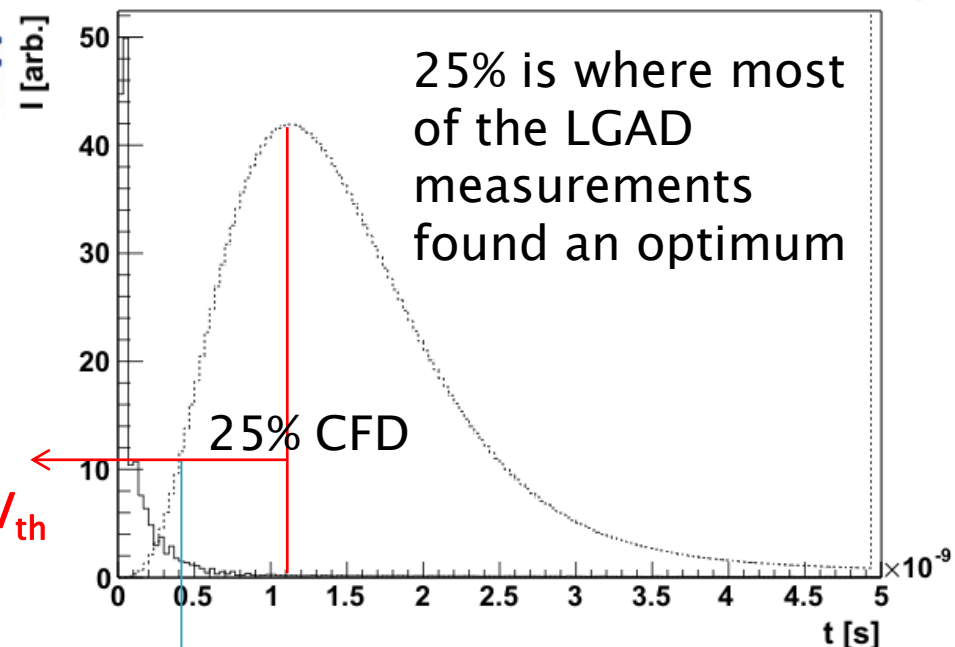
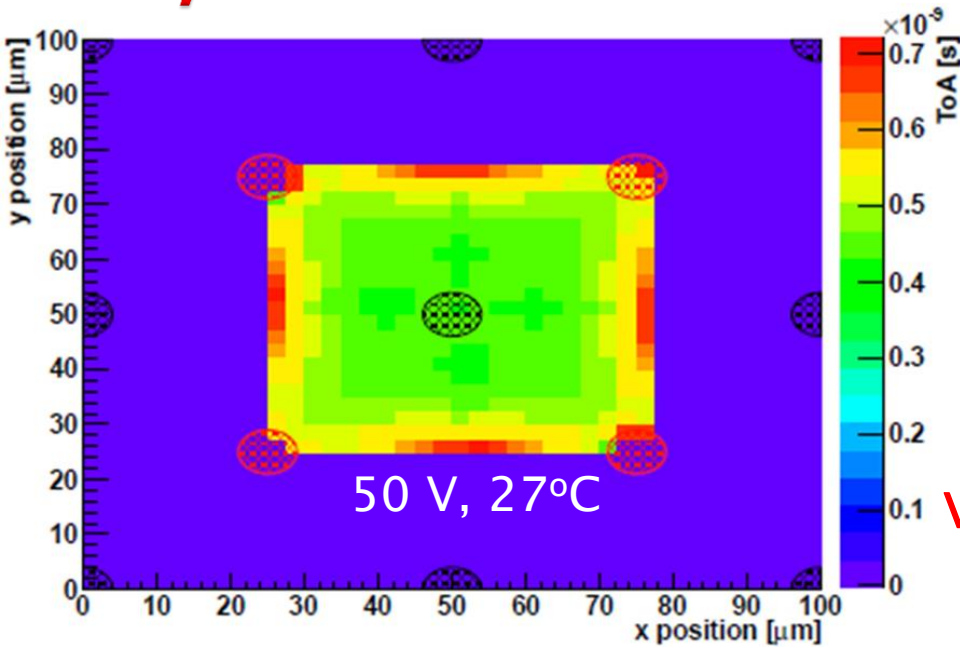
kdetsim.org



- KDetSim was used in three dimension to simulate detectors (see [indico.cern.ch/event/456679/contributions/1126324/](http://indico.cern.ch/event/456679/contributions/1126324/) ).
- solves Laplace ( $U_w$ ) and Poisson ( $U$ ) equations for given  $N_{eff}$  to get  $E, E_w$  and then performs drift in steps solving equation of motion
- Unirradiated sensors  $\rightarrow$  no trapping, no multiplication
- CR-RC<sup>3</sup> shaping with 1 ns peaking time - shaping type is not crucial

**Noise parameters that depend on electronics were not considered  $\rightarrow$  only time walk was studied!**

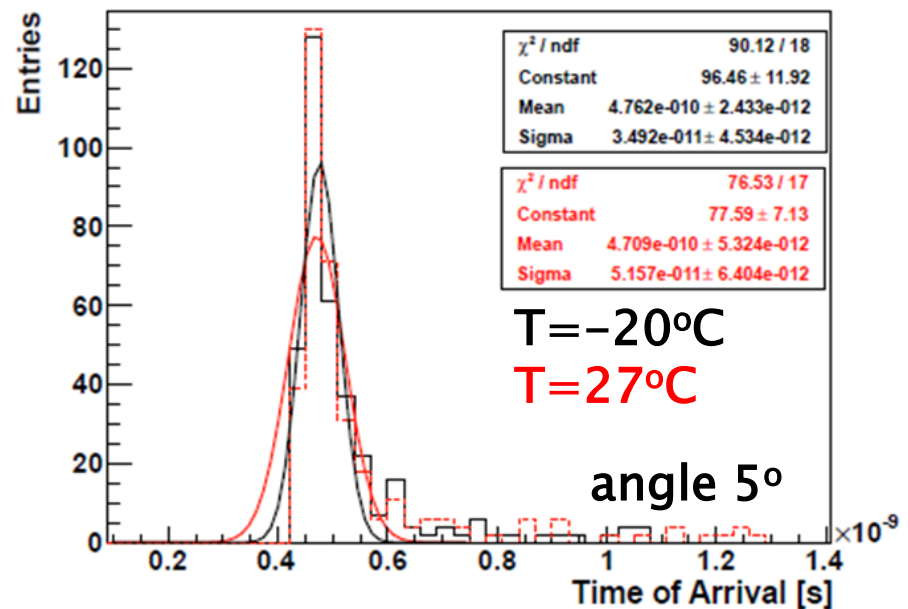
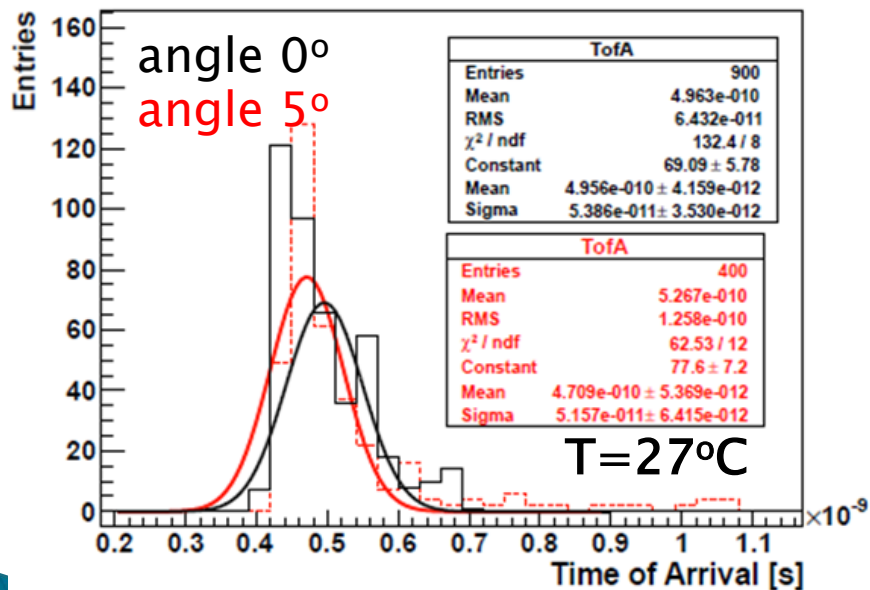
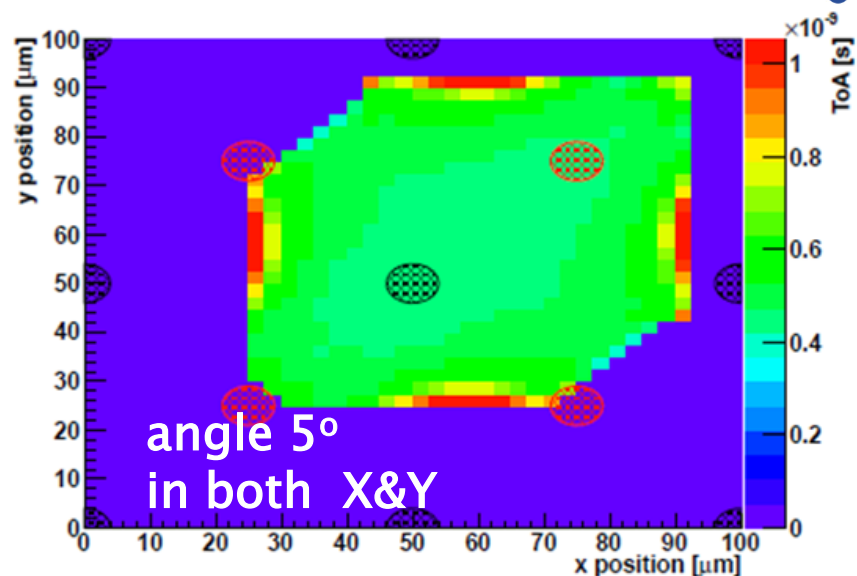
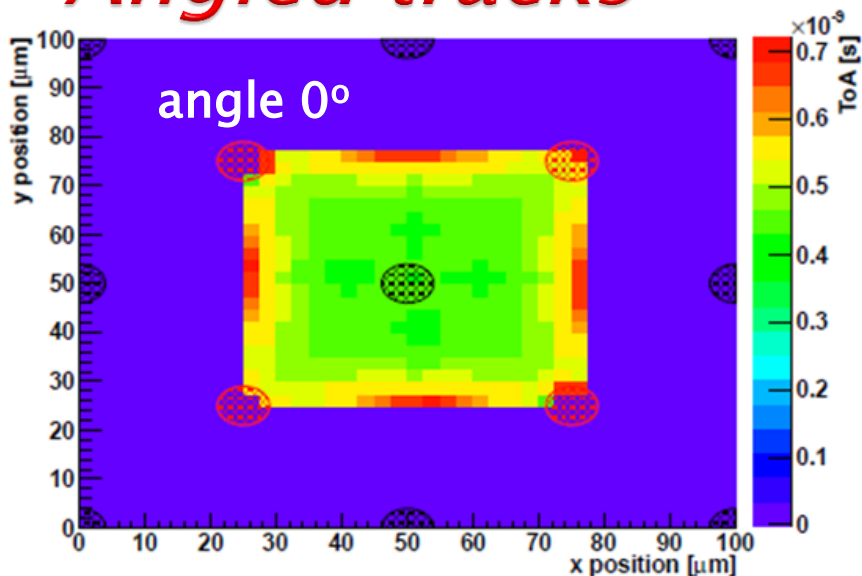
# Perpendicular tracks



ToA (time over amplitude/of arrival)

- ▶ at least 1000e is required to consider hit for analysis
- ▶ a uniform “simulation scan” over the surface shows areas of slower/faster signal
- ▶ Outer junction columns (black) are separate electrodes – individual cells

# Angled tracks

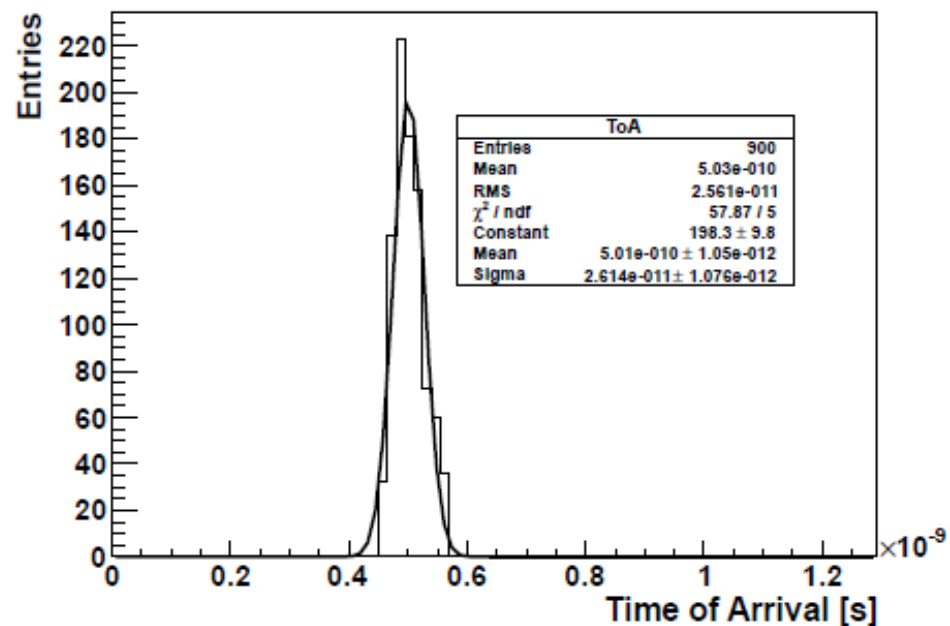
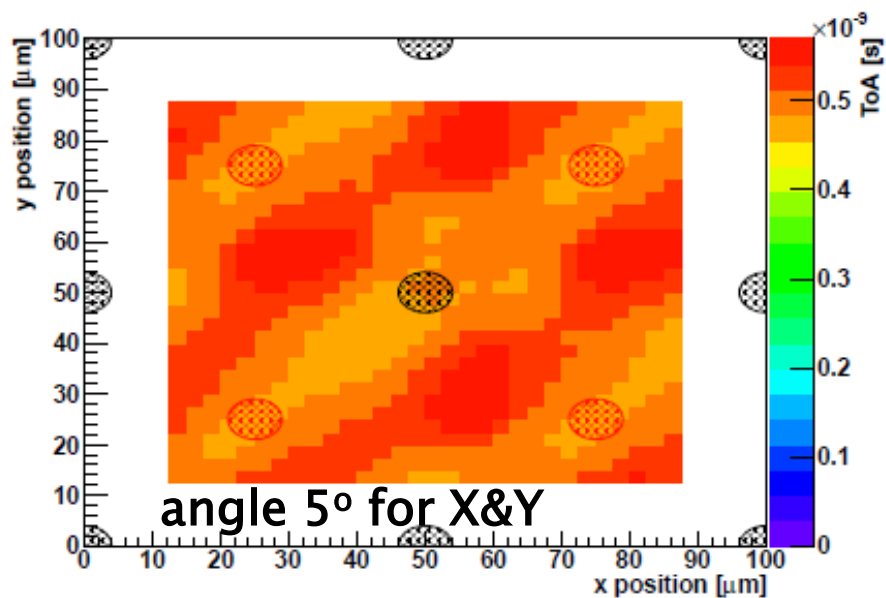


At lower temperature the decrease of ToA distribution is significant.  
At larger angle the width gets smaller although there are out layers.



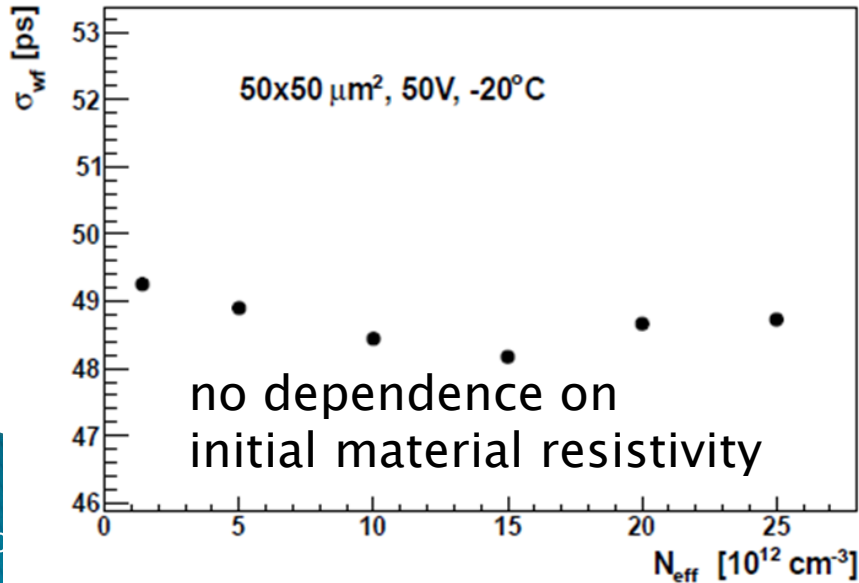
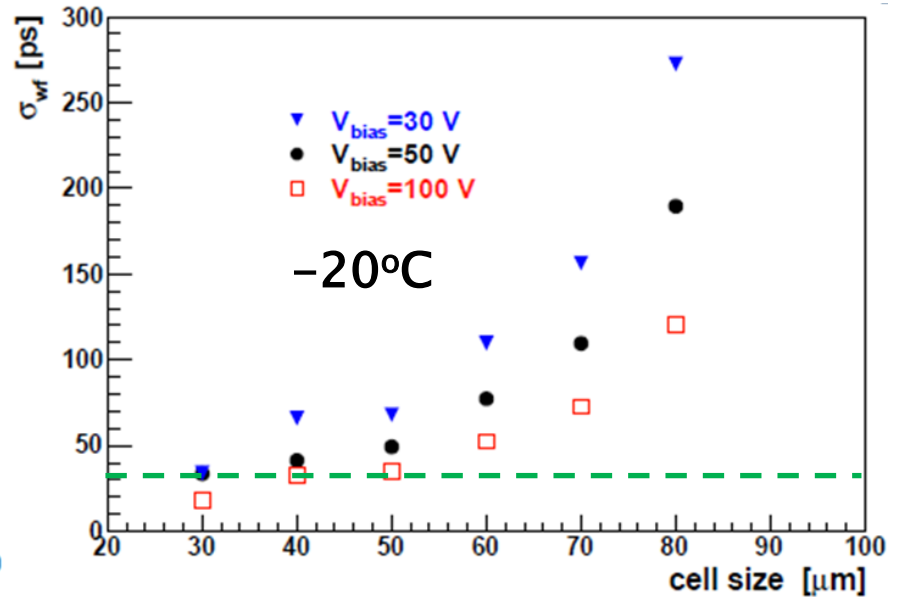
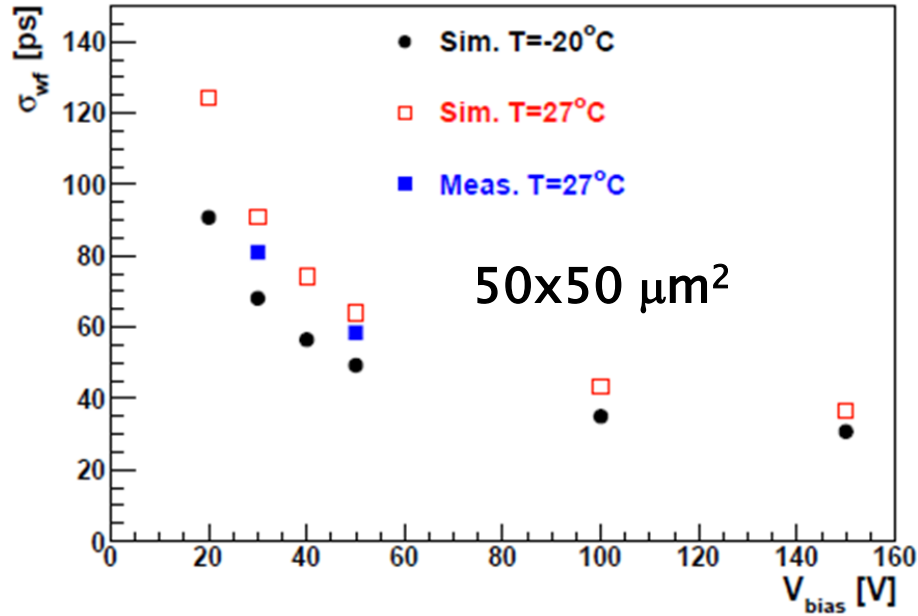


# Merging cells into single electrode



- ▶ all junction electrodes at the same weighting potential (no charge sharing between pixel cells anymore – much better performance)
- ▶ with tracks under angle (5° at  $r=30$  cm of ATLAS-HGTD) and  $T=27^\circ\text{C}$ .
- ▶ very good timing resolution ( $\sigma_{\text{TW}}$ ) of **26 ps – comparable to Landau fluctuations in 50  $\mu\text{m}$  LGAD ( $\sigma_{\text{Lf, LGAD}} \sim \sigma_{\text{wf, 3D}}$ )**
- ▶ at lower temperatures – this will improve even more

# Cell size, bias voltage, temperature



Even for single cell operation and  $\text{RMS}_{\text{wf}}$  instead of  $\sigma_{\text{wf}}$  (conservative)

- for bias voltages of  $>50$  V
- cell sizes  $\leq 50$   $\mu\text{m}$
- low temperatures  $< -20^\circ\text{C}$



time resolution  $\sim 30$  ps is achievable



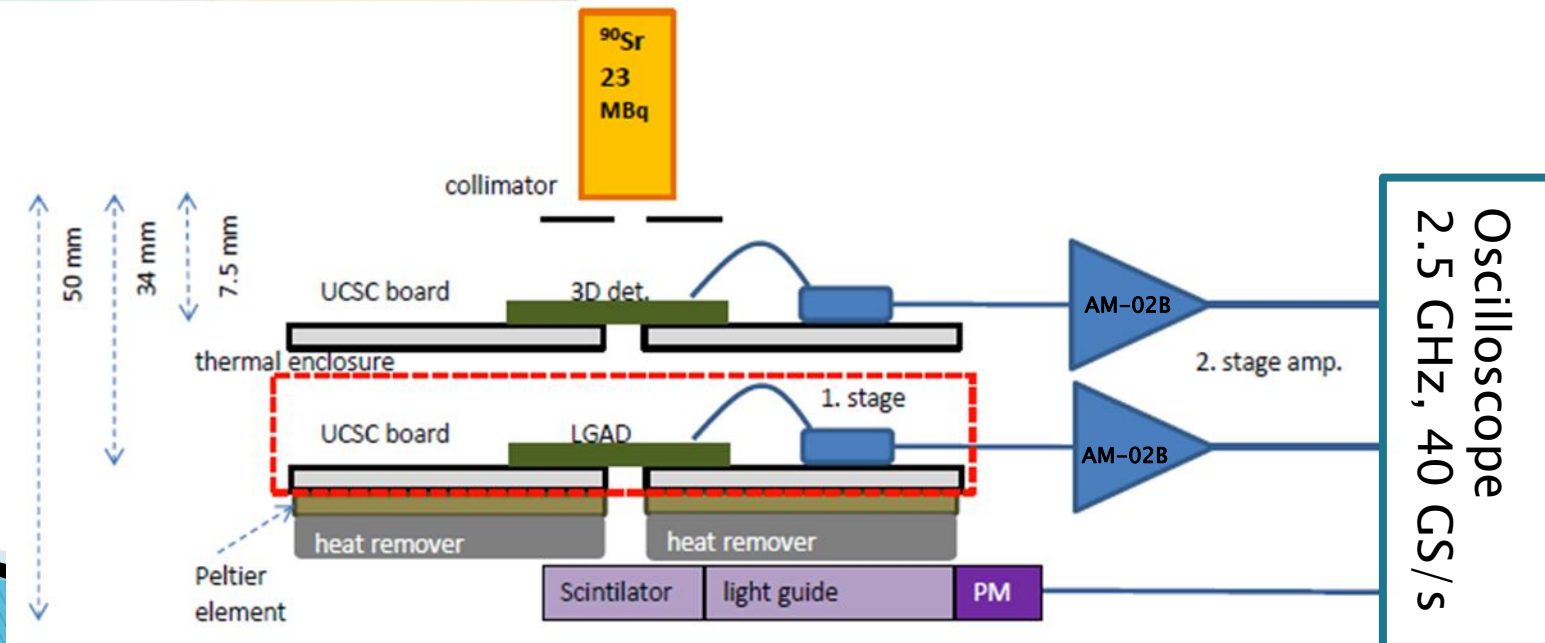
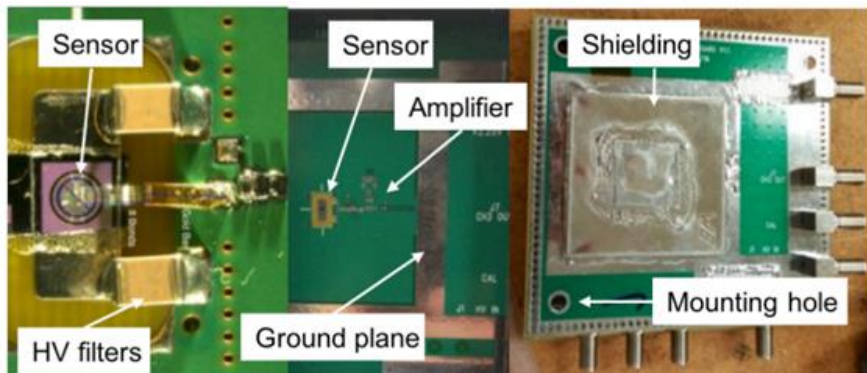
# *MEASUREMENT*

# Experimental setup

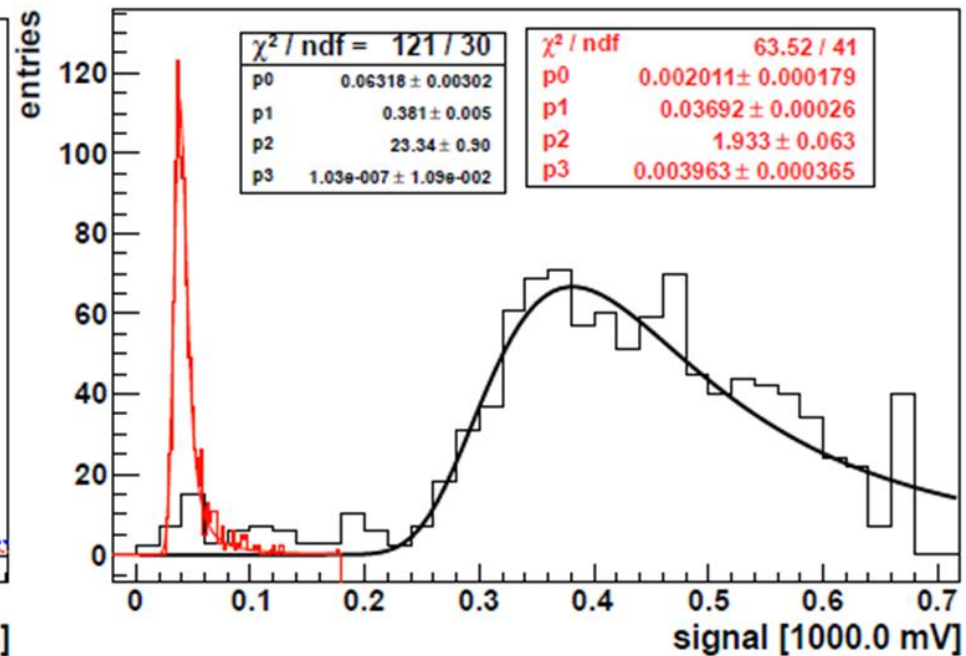
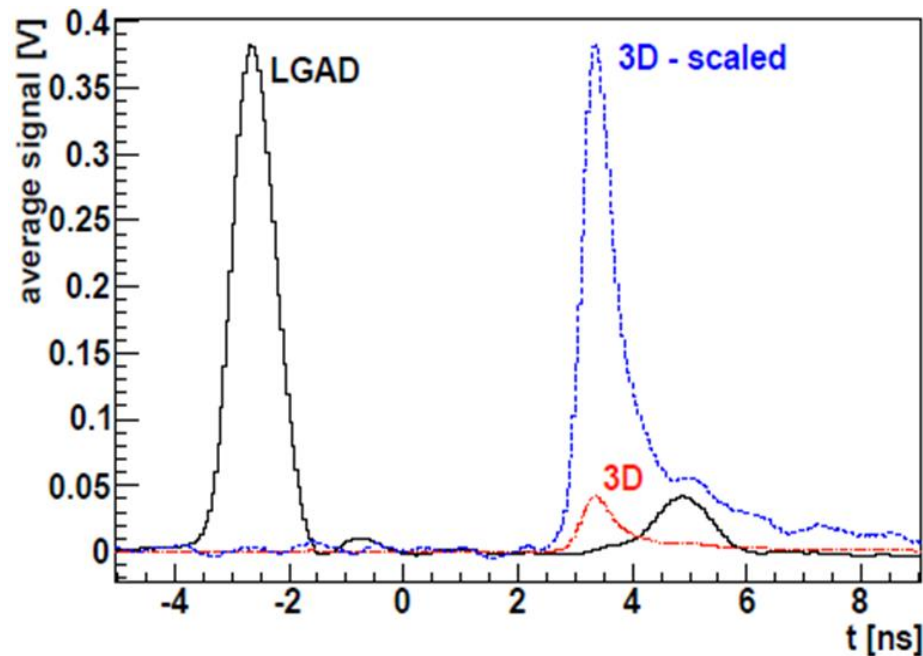


UCSC timing boards (same as for most of LGAD studies) used for measuring the signal followed by 35 dB Particulars amp

- ▶ required hits with very low threshold of 15 mV in both planes (extremely low rate ~1000/day)
- ▶ no scintillator+PM were used as this would even more reduce the rate
- ▶ 3D detectors were not cooled in these tests due to issues with rate/mounting



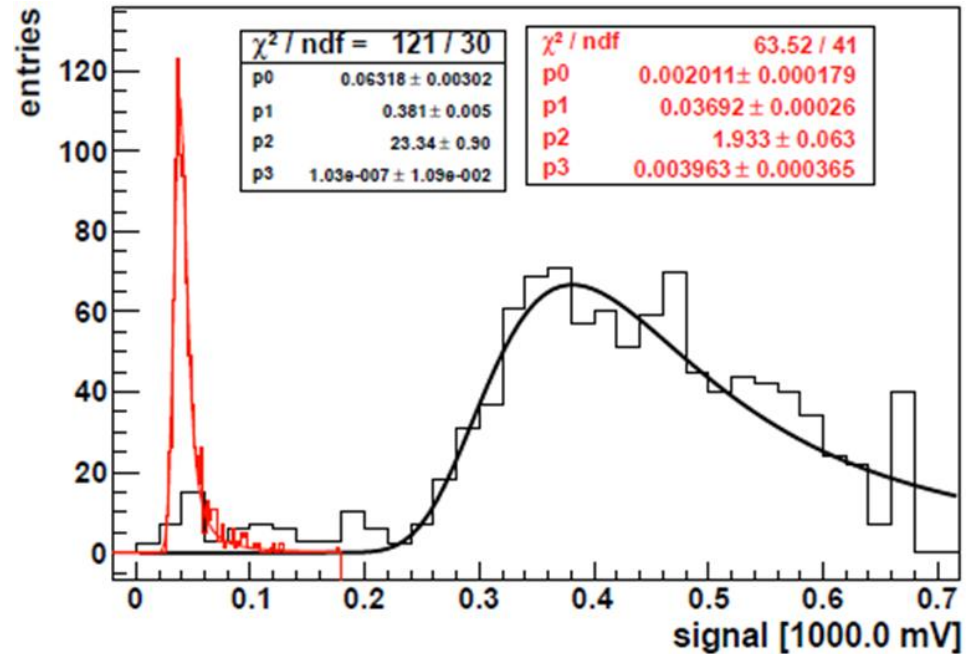
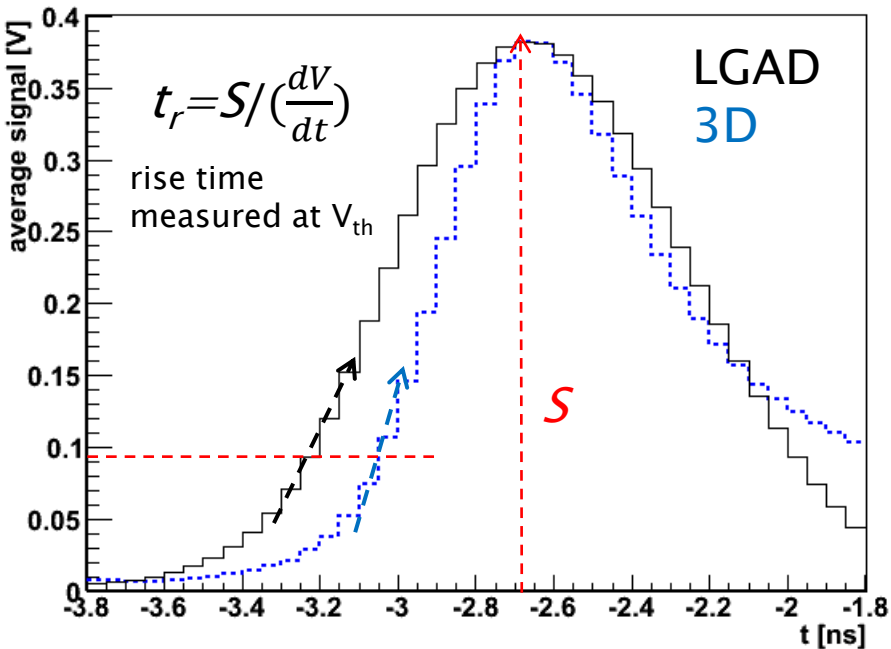
# Signal shape and charge



- ▶ Different shape of LGAD and 3D detector
  - longer tail of 3D
  - faster rise of LGAD
- ▶ Large difference in height due to large LGAD gain ( $G \sim 50-60$ ) - HPK50-D sensor

- ▶ Peak of the signal is sampled
  - around 9-10 times larger signal for LGAD
  - Signal calibrated with pin diode and corresponds to
- ▶ Signal of both is in agreement with expectations.

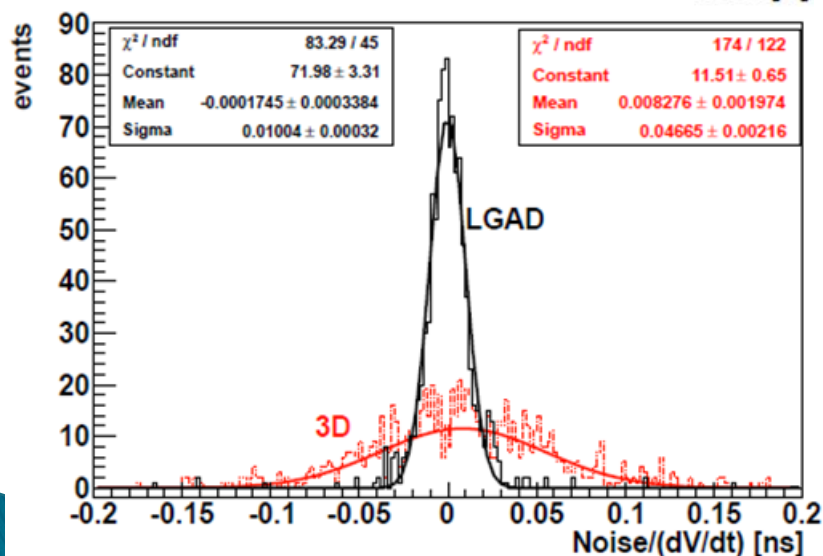
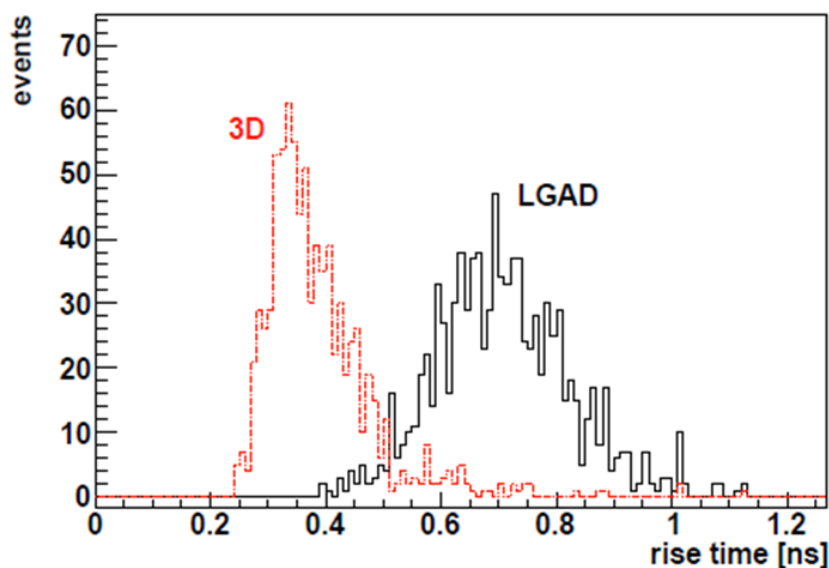
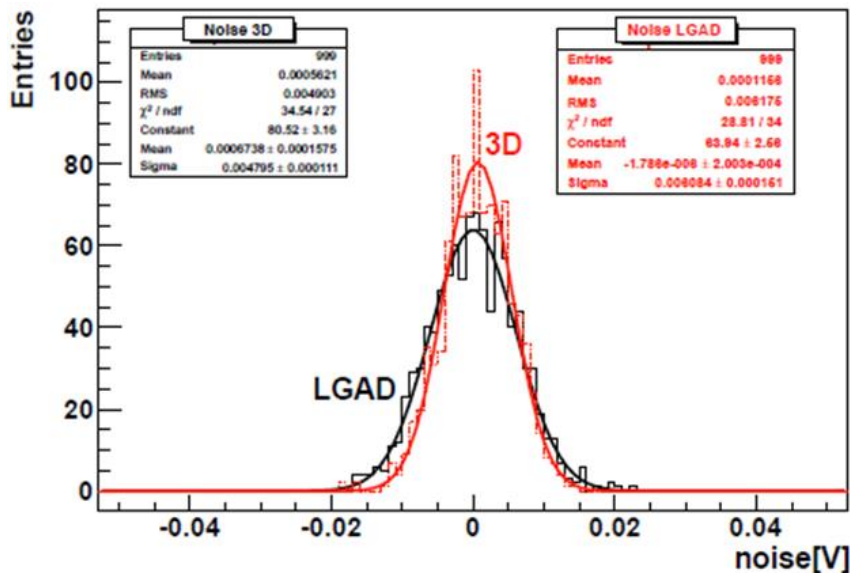
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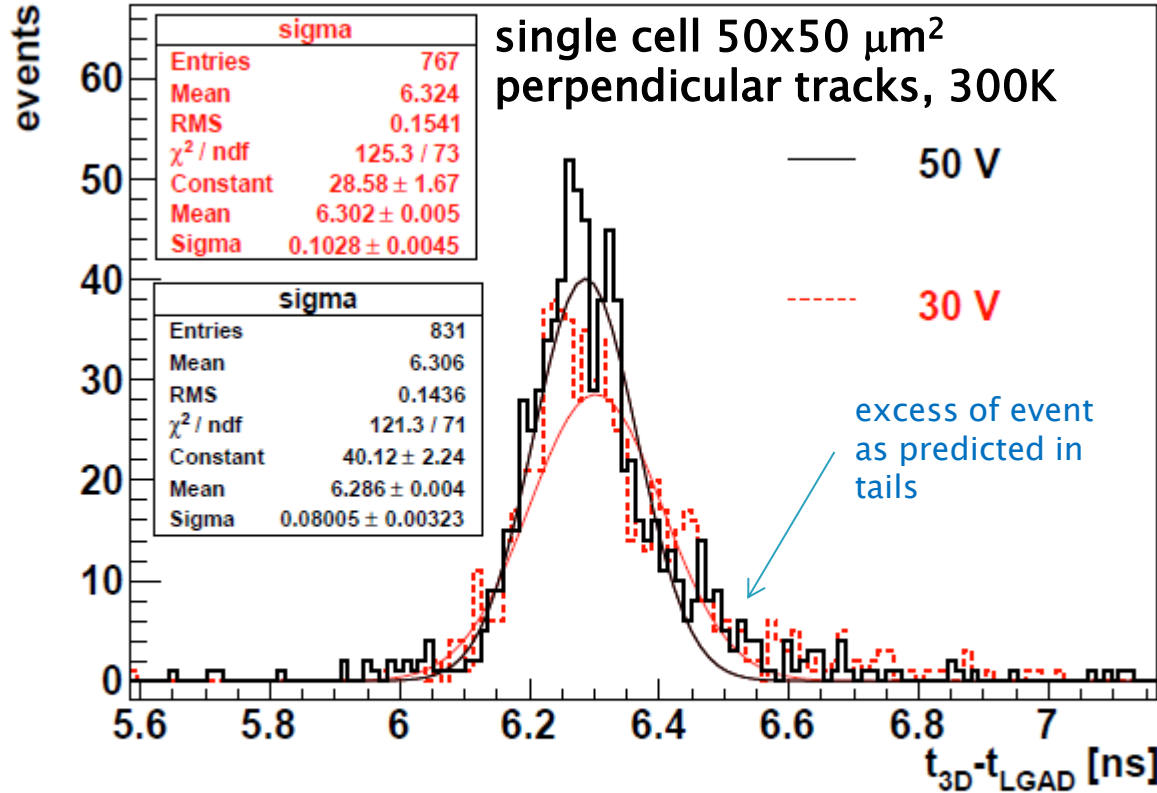
# Noise, rise time, jitter



- ▶ Noise is compatible with larger capacitance of LGAD ( $\sigma=6.0$  mV), wrt to 3D ( $\sigma=4.8$  mV)
- ▶ 3D detector is around twice faster than LGAD and that should reflect in the noise jitter:
  - difference in signal rise time  $\sim 2$
  - difference in signal  $\sim 9-10$
  - similar noise

Around 5 times larger jitter is expected for 3D and this is also confirmed (47 ps for 3D and 10 ps for LGAD)

# Timing resolution of 3D detectors



50 V:

$$\sigma_{wf, meas} = 58 \text{ ps}$$

$$\sigma_{wf, sim} = 54 \text{ ps}$$

$$RMS_{wf, sim} = 64 \text{ ps}$$

30 V:

$$\sigma_{wf, meas} = 81 \text{ ps}$$

$$\sigma_{wf, sim} = 89 \text{ ps}$$

$$RMS_{wf, sim} = 89 \text{ ps}$$

that confirms simulated results - within 10%

$$\sigma_t^2 = \sigma_{LGAD}^2 + \sigma_{3D}^2 \rightarrow \sigma_{3D} = \sqrt{80^2 \text{ps}^2 - 26^2 \text{ps}^2} = 75 \text{ ps}$$

$$\sigma_{wf}^2 \approx \sigma_{3D}^2 - \sigma_{3D,j}^2 \rightarrow \sigma_{wf} \approx \sqrt{75^2 \text{ps}^2 - 47^2 \text{ps}^2} \approx 58 \text{ ps}$$





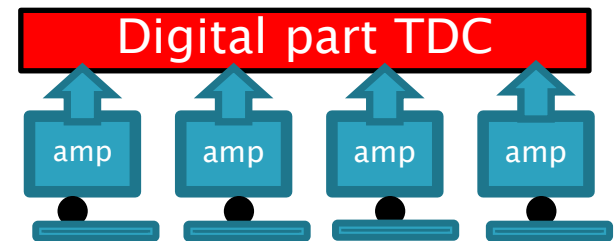
# *DISCUSSION*



# What does that mean for HL-LHC?

Can they be considered as a replacement for LGAD in harshest environments?

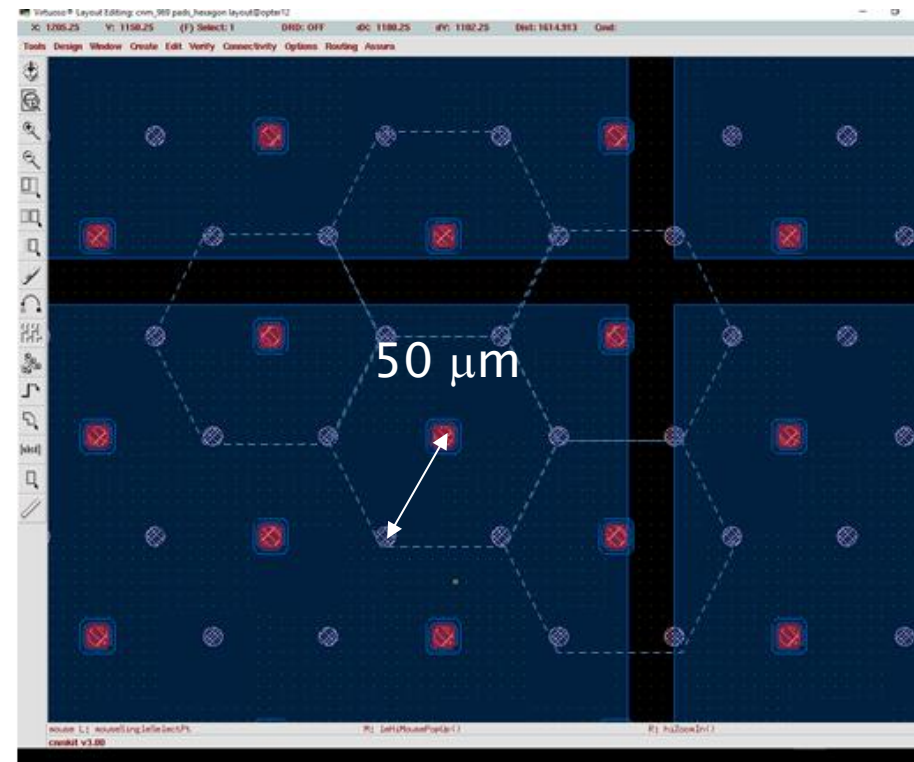
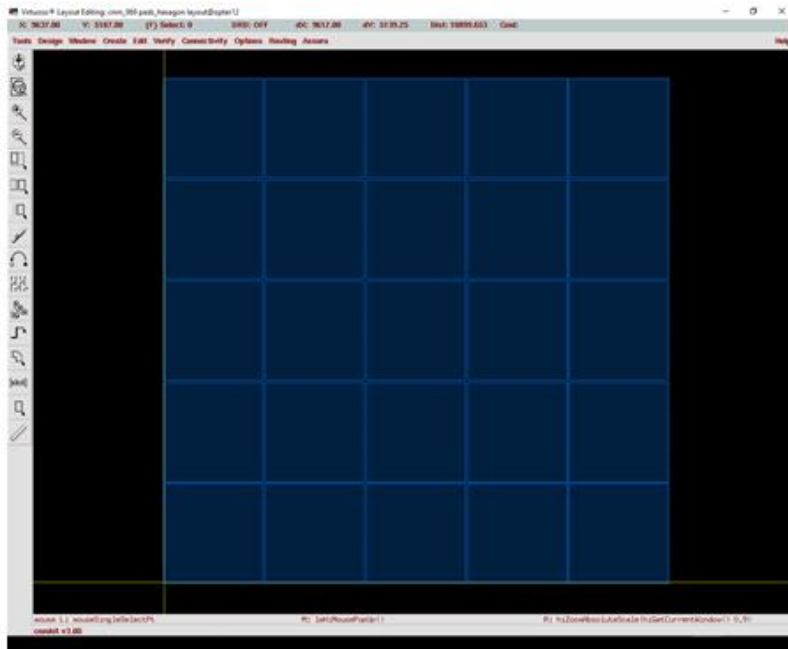
- ▶ We expect to have threshold (ALTIROC chip of ATLAS HGTD) of  $\sim 2$  fC ( $\sim 12600$  e) for LGADs so the signal would large enough MPV  $\sim 18000e$  at  $5 \cdot 10^{15} \text{ cm}^{-2}$  at  $V_{\text{bias}} < 150$  V.
- ▶ However the capacitance will be much larger ( $\sim 50 \times 50 \text{ um}^2$  pads 35 pF/cell  $\rightarrow$  1 mm<sup>2</sup> cell has  $\sim 14$  pF instead of  $\sim 3$  pF for LGAD)
  - that means lower gain of preamp or equivalent say larger ENC which will spoil the jitter
  - faster rise time will partially compensate for increase of jitter, but not entirely
  - also the threshold can change – this is yet to be seen with latest chip
- ▶ A way to prevent a problem with capacitance would be simply splitting a pixel into smaller ones. If floor-plan is to small then only analog part can be separated.  
There is no problem with fill factor.
- ▶ Also other pixel designs can reduce the capacitance.





# HL-LHC backup design

- ▶ less capacitance – hexagonal with cell dimension  $50\ \mu\text{m}$  for ganged cells – exact numbers will be subject to optimization
- ▶ more uniform fields – smaller breakdown
- ▶ better ratio low field/total area
- ▶ Can be thicker –  $500\ \mu\text{m}$  wafers will require larger holes diameters (maybe  $15\ \mu\text{m}$ ). The new Deep RIE available at the end of 2019 may solve the problem for CNM.





# Conclusions

- ▶ Timing in small cell  $50 \times 50 \mu\text{m}^2$  3D detectors was measured and simulated.
- ▶ Very good agreement between simulated and measured results was found, within 10%.
- ▶ Contribution to the timing resolution due to different hit positions is found to be comparable to Landau fluctuations in LGAD at high gain
  - For multi-cell operation the resolution of 26 ps at room temperature is predicted. Lowering the temperature improves timing even more
- ▶ Measurements open possibilities for backup solution for HL-LHC timing detectors providing that capacitance can be kept under control:
  - larger cells
  - smaller pads
  - multiple amplifiers per pad with common digital part to save floor space on the electronics